

54F/74F410 Register Stack—16 x 4 RAM TRI-STATE® Output Register

General Description

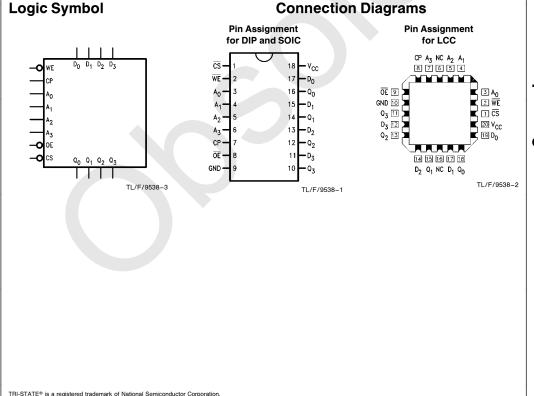
The 'F410 is a register-oriented high-speed 64-bit Read/ Write Memory organized as 16-words by 4-bits. An edgetriggered 4-bit output register allows new input data to be written while previous data is held. TRI-STATE outputs are provided for maximum versatility. The 'F410 is fully compatible with all TTL families.

Features

- Edge-triggered output register
- Typical access time of 35 ns
- TRI-STATE outputs
- Optimized for register stack operation
- 18-pin package
- 9410 replacement

Commercial	Military	Package Number	Package Description
74F410PC		N18A	18-Lead (0.300" Wide) Molded Dual-In-Line
	54F410DM (Note 1)	J18A	18-Lead Ceramic Dual-In-Line
74F410SC		M20B	20-Lead (0.300" Wide) Molded Small Outline, JEDEC
54F410LM		W20A	20-Lead Cerpak

Note 1: Military grade device with environmental and burn-in processing. Use suffix = DMQB, LMQB



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Unit Loading/Fan Out

			54F/74F
Pin Names	Description	U.L. HIGH/LOW	Input I _{IH} /I _{IL} Output I _{OH} /I _{OL}
$A_0 - A_3$	Address Inputs	1.0/1.0	20 µA/ −0.6 mA
$D_0 - D_3$	Data Inputs	1.0/1.0	20 µA/ −0.6 mA
CS	Chip Select Input (Active LOW)	1.0/2.0	20 μA/ −1.2 mA
ŌĒ	Output Enable Input (Active LOW)	1.0/1.0	20 µA/ −0.6 mA
WE	Write Enable Input (Active LOW)	1.0/1.0	20 µA/ −0.6 mA
CP	Clock Input (Outputs Change on		
	LOW-to-HIGH Transition)	1.0/2.0	20 μA/ −1.2 mA
$Q_0 - Q_3$	TRI-STATE Outputs	150/40 (33.3)	-3 mA/24 mA (20 mA)

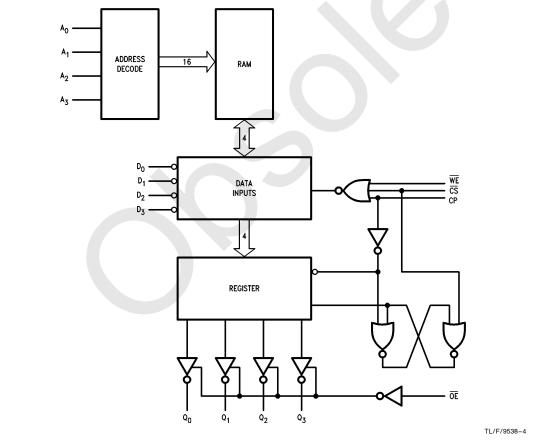
Functional Description

Write Operation—When the three control inputs, Write Enable (WE), Chip Select (\overline{CS}), and Clock (CP), are LOW the information on the data inputs (D_0-D_3) is written into the memory location selected by the address inputs (A_0-A_3). If the input data changes while \overline{WE} , \overline{CS} , and CP are LOW, the contents of the selected memory location follow these changes, provided setup and hold time criteria are met.

Read Operation—Whenever \overline{CS} is LOW and CP goes from LOW-to-HIGH, the contents of the memory location selected by the address inputs (A₀-A₃) are edge-triggered into the Output Register.

The (\overline{OE}) input controls the output buffers. When \overline{OE} is HIGH the four outputs (Q_0-Q_3) are in a high impedance or OFF state; when \overline{OE} is LOW, the outputs are determined by the state of the Output Register.

Block Diagram



Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature	-65°C to +150°C
Ambient Temperature under Bias	-55°C to +125°C
Junction Temperature under Bias Plastic	−55°C to +175°C −55°C to +150°C
V _{CC} Pin Potential to Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to $+7.0V$
Input Current (Note 2)	-30 mA to $+5.0$ mA
Voltage Applied to Output in HIGH State (with $V_{CC} = 0V$)	
Standard Output	-0.5V to V _{CC}
TRI-STATE Output	-0.5V to +5.5V
Current Applied to Output	
in LOW/ Chata (Max)	tuine the reted (meA)

Free Air Ambient Temperature Military

Conditions

Recommended Operating

in LOW State (Max) twice the rated I_{OL} (mA) Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

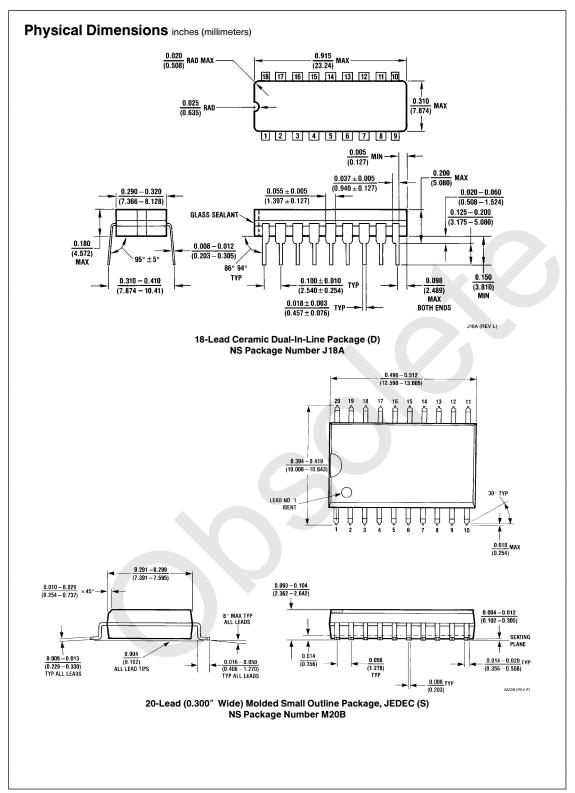
Note 2: Either voltage limit or current limit is sufficient to protect inputs.

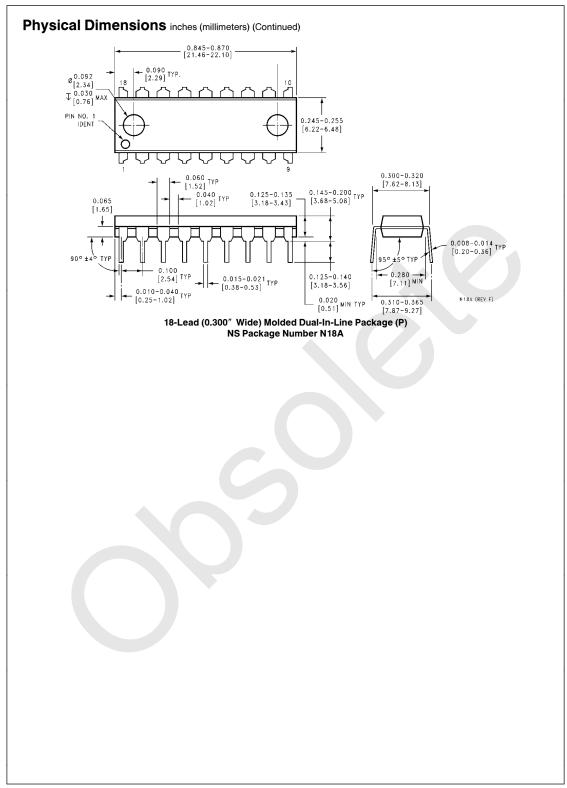
DC Electrical Characteristics

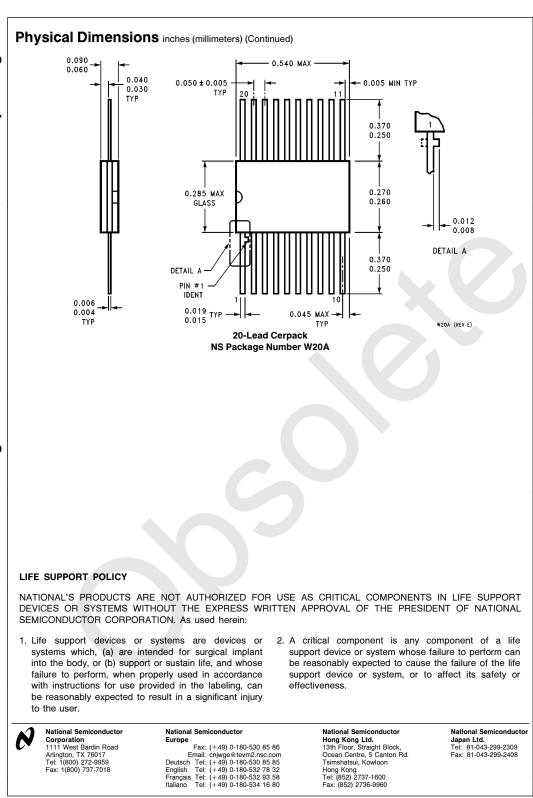
Symbol	Parameter		54F/74F			Units	Vcc	Conditions	
Symbol	Farane		Min	Тур	Max	Units	•CC	Conditions	
VIH	Input HIGH Voltage		2.0			v		Recognized as a HIGH Signa	
VIL	Input LOW Voltage				0.8	v		Recognized as a LOW Signa	
V _{CD}	Input Clamp Diode Vo	oltage			-1.2	v	Min	$I_{IN} = -18 \text{ mA}$	
V _{OH}	Output HIGH Voltage	54F 10% V _{CC} 54F 10% V _{CC} 74F 10% V _{CC} 74F 10% V _{CC} 74F 5% V _{CC}	2.5 2.4 2.5 2.4 2.7			v	Min	$\begin{split} I_{OH} &= -1 \text{ mA} \\ I_{OH} &= -3 \text{ mA} \\ I_{OH} &= -1 \text{ mA} \\ I_{OH} &= -3 \text{ mA} \\ I_{OH} &= -3 \text{ mA} \end{split}$	
V _{OL}	Output LOW Voltage	54F 10% V _{CC} 74F 10% V _{CC}			0.5 0.5	V	Min	$I_{OL} = 20 \text{ mA}$ $I_{OL} = 24 \text{ mA}$	
IIH	Input HIGH Current	54F 74F			20.0 5.0	μA	Max	$V_{IN} = 2.7V$	
I _{BVI}	Input HIGH Current Breakdown Test	54F 74F			100 7.0	μΑ	Max	$V_{IN} = 7.0V$	
ICEX	Output HIGH Leakage Current	54F 74F	7		250 50	μΑ	Max	$V_{OUT} = V_{CC}$	
V _{ID}	Input Leakage Test	74F	4.75			V	0.0	$I_{ID} = 1.9 \ \mu A$ All Other Pins Grounded	
I _{OD}	Output Leakage Circuit Current	74F			3.75	μΑ	0.0	V _{IOD} = 150 mV All Other Pins Grounded	
Ι _{ΙL}	Input LOW Current				-0.6 -1.2	mA	Max	$ \begin{array}{l} V_{\text{IN}} = 0.5 \text{V} \left(\text{A}_{\text{n}}, \text{D}_{\text{n}}, \overline{\text{OE}}, \overline{\text{WE}} \right) \\ V_{\text{IN}} = 0.5 \text{V} \left(\overline{\text{CS}}, \text{CP} \right) \end{array} $	
I _{OZH}	Output Leakage Curre	ent			50	μΑ	Max	$V_{OUT} = 2.7V$	
I _{OZL}	Output Leakage Curre	ent			-50	μΑ	Max	$V_{OUT} = 0.5V$	
I _{OS}	Output Short-Circuit (Current	-60		-150	mA	Max	$V_{OUT} = 0V$	
I _{ZZ}	Bus Drainage Test				500	μA	0.0V	$V_{OUT} = 5.25V$	

Symbol	Paramete	r		54F/74F		Units	V _{CC}	Cor	nditions
Cymbol	T aramete	•	Min	Тур	Max	onito	•00	001	landonio
ICCH	Power Supply Current			47	70	mA	Max	V _O =	= HIGH
I _{CCL}	Power Supply Current			47	70	mA	Max	V _O =	LOW
I _{CCZ}	Power Supply Current			47	70	mA	Max	V _O =	= HIGH Z
AC Ele	ctrical Characte	ristics							
		74F			54F		74F		-
Symbol	Parameter	${f T_A}=\ +\ {f V_{CC}}=\ +\ {f C_L}=\ 5$	- 5.0V		/ _{CC} = Mil = 50 pF		, V _{CC} = C C _L = 50 p		Units
		Min	Max	Min	Max	Mi	n	Мах	
t _{PLH} t _{PHL}	Propagation Delay CP to Q	3.0 3.5	8.5 9.0	2.5 3.0	11.0 12.0	2.5 3.0		9.5 10.0	ns
t _{PZH} t _{PZL}	Enable Time OE to Q	3.0 3.5	8.0 9.0	2.5 3.0	10.5 13.0	2.5		9.0 10.0	
t _{PHZ}	Disable Time	2.5	6.5	2.0	8.5	2.0		7.5	ns
t _{PLZ}	OE to Q	2.5	7.0	2.0	9.5	2.0)	8.0	
AC Op	erating Require	ments							
			74F		54F		74F	:	_
Symbol	Parameter		= +25°C = +5.0V	Т	$A, V_{CC} = M$	il	T _A , V _{CC} =	- Com	Unit
		Min	Max	Mi	n	Max	Min	Мах	
		45.0					17.0		
t _s (H) t _s (L)	Setup Time, HIGH or LO A _n to CP	N 15.0 15.0		23			17.0 17.0		
t _h (H)	Hold Time, HIGH or LOW	/ 0		0			0		ns
t _h (L)	A _n to CP	0		0			0		
RITE MODE	E								
t _s (H) t _s (L)	Setup Time, HIGH or LOV A _n to WE	W 0 0		0			0 0		
t _h (H) t _h (L)	Hold Time, HIGH or LOW A _n to WE	/ 0 0		0			0 0		– ns
t _s (H)	Setup Time, HIGH or LO	W 5.0		8.	5		6.0		
t _s (L) +. (⊔)		5.0		8.			6.0		ns
t _h (H) t _h (L)	Hold Time, HIGH or LOW D _n to WE	0		2.			0 0		
t _w	WE Pulse Width Required to Write	7.5		9.			8.5		ns
t _w	CS Pulse Width Required to Write	7.5		9.	5		8.5		ns
t _w	CP Pulse Width Required to Write	7.5		9.	5		8.5		ns
Note: Milita	ary temperature range for t	his device is	-40°C to +8	35°C.		I			

	<u>74F</u>	410	s c	X	
Temperature Range Family 74F = Commercial 54F = Military			ĪĪ	L	Special Variations X = Devices shipped in 13" reels QB = Military grade device with
Device Type					environmental and burn-in processing
Package Code P = Plastic DIP S = Small Outline (SOIC) D = Ceramic DIP L = Package Leadless Chip Carrier					Temperature Range $C = Commercial (0^{\circ}C to + 70^{\circ}C)$ $M = Military (-55^{\circ}C to + 125^{\circ}C)$
					0







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